

PNP SURFACE MOUNT TRANSISTOR

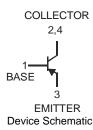
Features

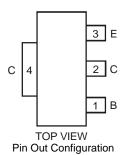
- **Epitaxial Planar Die Construction**
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)

Mechanical Data

- Case: SOT89-3L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.055 grams (approximate)







Maximum Ratings @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-50	V
Collector-Emitter Voltage	V _{CEO}	-50	V
Emitter-Base Voltage	V _{EBO}	-5	V
Continuous Collector Current	Ic	-2	А
Base Current	I _B	-0.4	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ T _A = 25°C	P _D	1	W
Thermal Resistance, Junction to Ambient Air (Note 3) @ T _A = 25°C	$R_{ heta JA}$	125	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

- 1. No purposefully added lead.
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 Device mounted on FR-4 PCB; pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.



Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic		Symbol	Min	Тур	Max	Unit	Conditions
OFF CHARACTERISTIC	OFF CHARACTERISTICS (Note 4)						
Collector-Base Breakdown Voltage		V _{(BR)CBO}	-50	_	_	V	$I_C = -100 \mu A, I_E = 0$
Collector-Emitter Breakdo	own Voltage	V _{(BR)CEO}	-50			V	$I_C = -10 \text{mA}, I_B = 0$
Emitter-Base Breakdown	Voltage	V _{(BR)EBO}	-5	_	_	V	$I_E = -100 \mu A, I_C = 0$
Collector Cut-Off Current		I _{CBO}	_	_	-0.1	μΑ	$V_{CB} = -50V, I_{E} = 0$
Emitter Cut-Off Current		I _{EBO}	_	_	-0.1	μΑ	$V_{EB} = -5V, I_{C} = 0$
ON CHARACTERISTICS	(Note 4)						
Collector-Emitter Saturation Voltage		V _{CE(SAT)}			-0.5	V	$I_C = -1A$, $I_B = -50mA$
Base-Emitter Saturation \	/oltage	V _{BE(SAT)}			-1.2	V	$I_C = -1A$, $I_B = -50mA$
	2DA1213O		70		140	_	$V_{CE} = -2V, I_{C} = -0.5A$
DC Current Gain	2DA1213Y	h _{FE}	120	_	240	_	$V_{CE} = -2V, I_{C} = -0.5A$
	2DA1213O, 2DA1213Y		20	_	_	_	V _{CE} = -2V, I _C = -2A
SMALL SIGNAL CHARA	SMALL SIGNAL CHARACTERISTICS						
Transition Frequency		f_T	_	160	_	MHz	$V_{CE} = -2V$, $I_{C} = -100$ mA, $f = 100$ MHz
Output Capacitance		C _{obo}	_	17		pF	$V_{CB} = -10V$, $I_E = 0$, $f = 1MHz$
SWITCHING CHARACTERISTICS							
Turn-On Time		t _{on}	_	25		ns	V 2V I 4A
Storage Time		ts	_	130	_	ns	$V_{CE} = -2V, I_{C} = -1A,$ $I_{B1} = -I_{B2} = -50\text{mA}$
Fall Time		t _f	_	12	_	ns	181 = -182 = -30111A

Notes: 4. Measured under pulsed conditions. Pulse width = $300\mu s$. Duty cycle $\leq 2\%$.

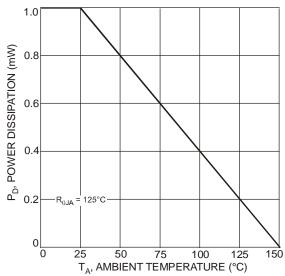


Fig. 1 Power Dissipation vs. Ambient Temperature

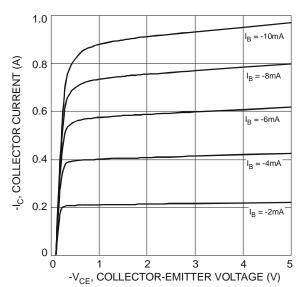


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage



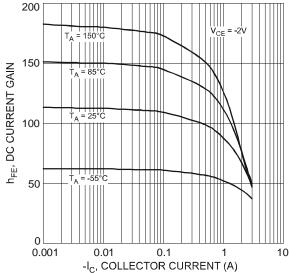


Fig. 3 Typical DC Current Gain vs. Collector Current (2DA12130)

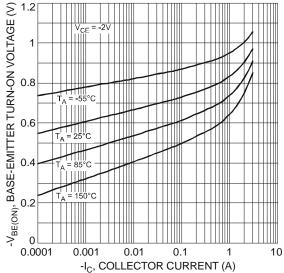


Fig. 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current

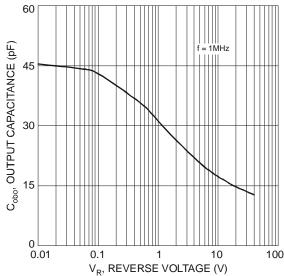


Fig. 7 Typical Output Capacitance Characteristics

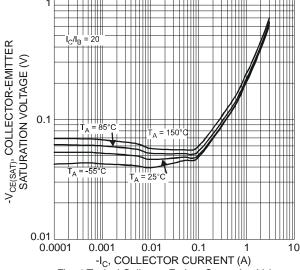


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

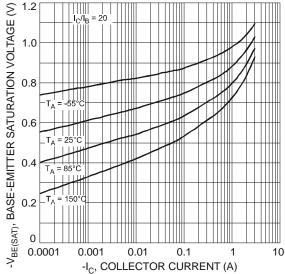


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

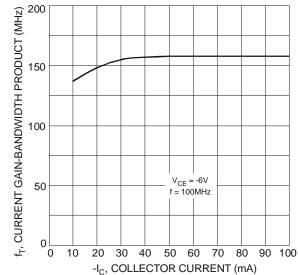


Fig. 8 Typical Gain-Bandwidth Product vs. Collector Current

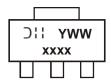


Ordering Information (Note 5)

Part Number	Case	Packaging
2DA1213O-13	SOT89-3L	2500/Tape & Reel
2DA1213Y-13	SOT89-3L	2500/Tape & Reel

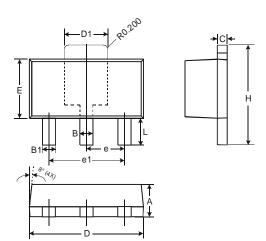
Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



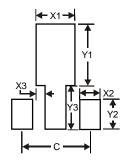
xxxx = Product Type Marking Code: P25X = 2DA1213O P25Y = 2DA1213Y YWW = Date Code Marking Y = Last digit of year (ex: 7 = 2007) WW = Week code 01 - 53

Package Outline Dimensions



SOT89-3L			
Dim	Min	Max	
Α	1.40	1.60	
В	0.44	0.62	
B1	0.35	0.54	
С	0.35	0.43	
D	4.40	4.60	
D1	1.52	1.83	
Е	2.29	2.60	
е	e 1.50 Typ		
e1	3.00 Typ		
Н	3.94	4.25	
L	0.89	1.20	
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
X1	1.7
X2	0.9
Х3	0.4
Y1	2.7
Y2	1.3
Y3	1.9
С	3.0



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Офис по работе с юридическими лицами:

105318, г. Москва, ул. Щербаковская д. 3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru moschip.ru_6 moschip.ru_4 moschip.ru_9